L Number	Hits	Search Text	DB	Time stamp
1	0	(gate near electrode)and ("0.1" near micrometer)and (patterning) and (shruken or reduced) with (low near K near dieelctric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
8	0	(gate near electrode)and ("0.1" near micrometer)and (patterning) and (shrunken or reduced) with (low near K near dieelctric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
15	0	(gate near electrode)and ("0.1" near micrometer)and (patterning) and (shrunken or reduced) with (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
22	0	(gate near electrode)and (patterning) and (shrunken or reduced) with (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:36
29	0	(gate near electrode)and (patterning)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:36
36	10	(gate)and (patterning)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:37
50	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("0.1" near micromeer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:38
57	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("0.1" near micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:38
43	8	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:42
64	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and (fine near pattern)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:43
71	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("100" near nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:47
78	0	(gate)and (patterning)and (low near K near dielectric) with mask and ("100" near nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:48
85	9	(gate)and (patterning)and ("100" near nanometer)and (low near K near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:48

92	5	(gate)and (patterning)and ("100" near nanometer)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:51
99	751849	(gate)withand ("100" near nanometer)and (patterning)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:52
106	0	(gate)with ("100" near nanometer)and (patterning)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:53
113	0	(gate)and (patterning)with ("100" near nanometer)and (feature near size) and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:54
120	1	(gate)and (patterning)with ("100" near nanometer)and (feature) and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:22
127	2	(gate)and (patterning)with ("100" near nanometer)and (feature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:28
134	7	"5648293"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:25
141	1	"6358856"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	(gate near electrode)and ("O.1" near micrometer)and (patterning) and (shruken or reduced) with (low near K near dieelctric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
2	BRS	L8	0	(gate near electrode)and ("O.1" near micrometer)and (patterning) and (shrunken or reduced) with (low near K near dieelctric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
3	BRS	L15	0	(gate near electrode)and ("O.1" near micrometer)and (patterning) and (shrunken or reduced) with (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:35
4	BRS	L22	0	(gate near electrode)and (patterning) and (shrunken or reduced) with (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:36
5	BRS	L29	0	(gate near electrode)and (patterning)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:36

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L36	10	(gate)and (patterning)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:37
7	BRS	L50	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("0.1" near micromeer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:38
8	BRS	L57	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("0.1" near micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:38
9	BRS	L43	8	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:42
10	BRS	L64	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and (fine near pattern)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L71	0	(gate)and (patterning)and (shrunken or reduce$2)and (low near K near dielectric) with mask and ("100" near nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:47
12	BRS	L78	0	(gate)and (patterning)and (low near K near dielectric) with mask and ("100" near nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:48
13	BRS	L85	9	(gate)and (patterning)and ("100" near nanometer)and (low near K near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:48
14	BRS	L92	5	(gate)and (patterning)and ("100" near nanometer)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:51
15	BRS	L99	751849	(gate)withand ("100" near nanometer)and (patterning)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:52

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L106	0	(gate)with ("100" near nanometer)and (patterning)and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:53
17	BRS	L113	0	(gate)and (patterning)with ("100" near nanometer)and (feature near size) and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 09:54
18	BRS	L120	1	(gate)and (patterning)with ("100" near nanometer)and (feature) and (low near K near dielectric) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:22
19	BRS	L127	2	(gate)and (patterning)with ("100" near nanometer)and (feature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:28
20	BRS	L134	7	"5648293"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:25

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L141	1	"6358856"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/01 10:29